NSN 5961-01-110-4296

Transistor - Page 1 of 2



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Inclosure Material:

Metal

Overall Length:

1.573 inches

Overall Height:

Between 0.250 inches and 0.450 inches

Overall Width:

1.050 inches

End Application:

Xm2

Mounting Facility Quantity:

2

Internal Configuration:

Junction contact

Joint Electronic Device Engineering Council/jedec/case Outline Designation:

To-3

Electrode Internally-electrically Connected To Case:

Cathode

Mounting Method:

Unthreaded hole

Semiconductor Material:

Silicon

Voltage Rating In Volts Per Characteristic:

120.0 breakdown voltage, collector-to-base, emitter open and 120.0 breakdown voltage, collector-to-emitter, base open and 5.0 emitter

to base voltage, static, collector open

Current Rating Per Characteristic:

Between 1.00 amperes source cutoff current and 30.00 amperes source cutoff current

Power Rating Per Characteristic:

200.0 watts small-signal input power, common-collector absolute

Transfer Ratio:

200.0 static forward current transfer ratio, common-emitter

Maximum Operating Tempurature Per Measurement Point:

200.0 degrees celsius ambient air

Special Features:

Junction pattern arrangement: npn

Terminal Type And Quantity:

2 pin

Shelf Life:

N/a

Unit Of Measure:

Demilitarization:

No

NSN 5961-01-110-4296 Transistor - Page 2 of 2

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